

INTEGRATED CIRCUIT DEVICES INCLUDING A MIM CAPACITOR

ABSTRACT OF THE DISCLOSURE

Integrated circuit devices include an integrated circuit substrate and a conductive lower electrode layer of a Metal-Insulator-Metal (MIM) capacitor on the integrated circuit substrate. A dielectric layer is on the lower electrode layer and a conductive upper electrode layer of the MIM capacitor is on the dielectric layer. A  
5 first intermetal dielectric layer is on the upper electrode layer. The first intermetal dielectric layer includes at least one via hole extending to the upper electrode layer. A first conductive interconnection layer is on the at least one via hole of the first intermetal dielectric layer. A second intermetal dielectric layer is on the first intermetal dielectric layer. The second intermetal dielectric layer includes at least one  
10 via hole extending to the first conductive interconnection layer and at least partially exposing the at least one via hole of the first intermetal dielectric layer. A second conductive interconnection layer is provided in the at least one via hole of the second intermetal dielectric layer that electrically contacts the first conductive interconnection layer.

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